

VERSION WITH MARKINGS TO SHOW CHANGES MADE

- 09933304.082001
1. (amended) A CMP process for a contact hole [and/]or metal track etching, in which a liner [(2)] deposited over the whole area on a dielectric [(1)] after the patterning and a metalization layer deposited over the whole area on the liner [(2)], said metalization layer preferably being composed of tungsten or copper, are removed in regions by a chemical mechanical polishing process (CMP) which stops on the dielectric [(1)],
wherein

at least in the regions surrounding the patterned portions on the dielectric [(1)], an auxiliary layer [(4)] which can easily be removed by the CMP process is fashioned between dielectric [(1)] and liner [(2)].
 2. (amended) The CMP process as claimed in claim 1,
wherein

the auxiliary layer [(4)] has a layer thickness in the range of 20 to 100 nm.
 3. (amended) The CMP process as claimed in [one of the preceding claims] claim 1,
wherein

the auxiliary layer [(4)] is used at least partly as a hard mask for the patterning [-] and preceding the etching [-] by dry etching.
 4. (amended) The CMP process as claimed in [one of the preceding claims] claim 1,
wherein

the reaching of the auxiliary layer [(4)] is detected by an etching stop detection signal during the CMP process.

5. (amended) The CMP process as claimed in [one of the preceding claims] claim 1, wherein
an additional wet-chemical cleaning step is carried out at the end of the etching.

6. (amended) The CMP process as claimed in [one of the preceding claims] claim 1, wherein
the auxiliary layer [(4)] is composed of diamond-like carbon, carbon polymers or of porous material.

7. (amended) The CMP process as claimed in claim 6, wherein
the auxiliary layer [(4)] is used in conjunction with a CARL resist as bottom resist.

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